Philips Semiconductors

Data sheet	
status	Product specification
date of issue	April 1995

BSP225
P-channel enhancement mode vertical D-MOS transistor

FEATURES

- Low $R_{DS(on)}$
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

DESCRIPTION

P-channel enhancement mode vertical D-MOS transistor in a miniature SOT223 envelope, intended for use in relay, high-speed and line transformer drivers.

PINNING - SOT223

PIN	DESCRIPTION
1	gate
2	drain
3	source
4	drain

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$-V_{DS}$	drain-source voltage		250	V
$-I_D$	drain current	DC value	225	mA
$R_{DS(on)}$	drain-source on-resistance	$-I_D = 200$ mA $-V_{GS} = 10$ V	15	Ω
$-V_{GS(th)}$	gate-source threshold voltage	$-I_D = 1$ mA $V_{GS} = V_{DS}$	2.8	V

PIN CONFIGURATION

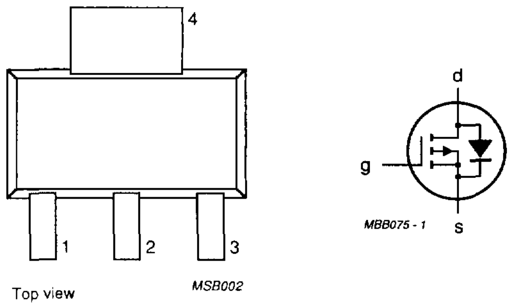

Fig.1 Simplified outline and symbol.

FOR MORE DETAILED INFORMATION SEE THE LATEST ISSUE OF HANDBOOK SC07 OR DATA SHEET